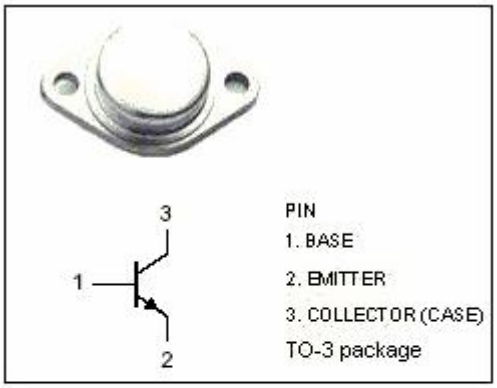
SPTECH Silicon NPN Power Transistor 2SC937

DESCRIPTION

- High Breakdown Voltage-
  : V_{CBO}= 1200V(Min)
- High Reliability

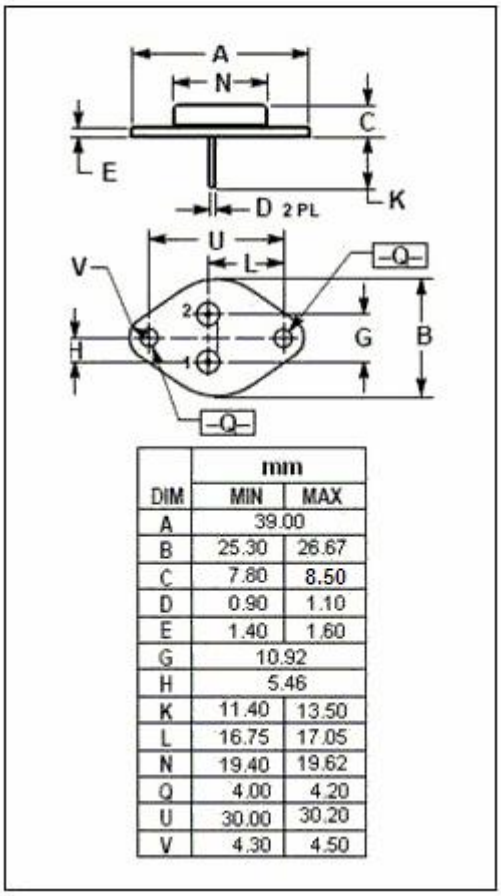


APPLICATIONS

- Designed for TV horizontal deflection output applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1200	V
V_{CEO}	Collector-Emitter Voltage	500	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current- Continuous	2.5	A
I_{CP}	Collector Current-Pulse	6	A
P_C	Collector Power Dissipation @ T_C= 25℃	22	W
T_J	Junction Temperature	125	℃
T_{stg}	Storage Temperature Range	-45~125	℃



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.40	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 10mA; R_{BE}= ∞	500			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 2.5A; I_B= 0.8A			5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 2.5A; I_B= 0.8A			1.8	V
I_{CBX}	Collector Cutoff Current	V_{CB}= 1200V; V_{EB}= 1.5V			1	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 6V; I_C= 0			0.2	mA
t_f	Fall Time	I_C= 2.5A, I_{B1}= 0.8A, I_{B2}= -1.1A; L_B= 10 μ H			1.2	μ s